

# FDP4020P/FDB4020P

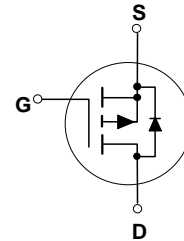
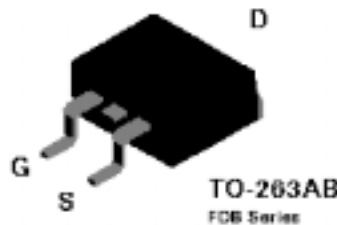
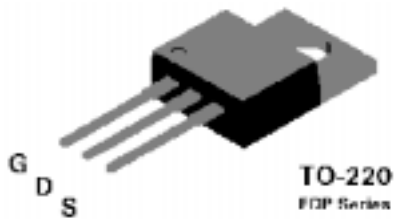
## P-Channel 2.5V Specified Enhancement Mode Field Effect Transistor

### General Description

This P-Channel low threshold MOSFET has been designed for use as a linear pass element for low voltage outputs. In addition, the part may be used as a low voltage load switch when switching outputs on or off for power management. The part may also be used in conjunction with DC-DC converters requiring P-Channel.

### Features

- -16 A, -20 V.  $R_{DS(on)} = 0.08 \Omega @ V_{GS} = -4.5 \text{ V}$   
 $R_{DS(on)} = 0.11 \Omega @ V_{GS} = -2.5 \text{ V}$ .
- Critical DC electrical parameters specified at elevated temperature.
- High density cell design for extremely low  $R_{DS(on)}$ .
- TO-220 and TO-263 (D<sup>2</sup>PAK) package for both through hole and surface mount applications.
- 175°C maximum junction temperature rating.



### Absolute Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	FDP4020P	FDB4020P	Units
V <sub>DSS</sub>	Drain-Source Voltage	-20		V
V <sub>GSS</sub>	Gate-Source Voltage	±8		V
I <sub>D</sub>	Drain Current - Continuous	-16		A
	- Pulsed	-48		
P <sub>D</sub>	Total Power Dissipation @ T <sub>C</sub> = 25°C	37.5		W
	Derate above 25°C	0.25		W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	-65 to +175		°C

### Thermal Characteristics

Symbol	Parameter	FDP4020P	FDB4020P	Units
R <sub>θJC</sub>	Thermal Resistance, Junction-to- Case	4		°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction-to- Ambient (Note 1)	62.5	40	°C/W

### Package Outlines and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
FDP4020P	FDP4020P	13"	12mm	2500 units

**Electrical Characteristics** $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off Characteristics**

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		-28		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 8\text{ V}, V_{DS} = 0\text{ V}$			100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -8\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

**On Characteristics** (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-0.4	-0.58	-1	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		2		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -4.5\text{ V}, I_D = -8\text{ A}$ , $V_{GS} = -4.5\text{ V}, I_D = -8\text{ A}, T_J = 125^\circ\text{C}$ $V_{GS} = -2.5\text{ V}, I_D = -7\text{ A}$		0.068 0.098 0.096	0.08 0.13 0.110	$\Omega$
$I_{D(on)}$	On-State Drain Current	$V_{GS} = -4.5\text{ V}, V_{DS} = -5\text{ V}$	-20			A
$g_{FS}$	Forward Transconductance	$V_{DS} = -5\text{ V}, I_D = -8\text{ A}$		14		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}$ , $f = 1.0\text{ MHz}$		665		pF
$C_{oss}$	Output Capacitance			270		pF
$C_{riss}$	Reverse Transfer Capacitance			70		pF

**Switching Characteristics** (Note 2)

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -5\text{ V}, I_D = -1\text{ A}$ , $V_{GS} = -4.5\text{ V}, R_{GEN} = 6\ \Omega$		8	16	ns
$t_r$	Turn-On Rise Time			24	38	ns
$t_{d(off)}$	Turn-Off Delay Time			50	80	ns
$t_f$	Turn-Off Fall Time			29	45	ns
$Q_g$	Total Gate Charge	$V_{DS} = -5\text{ V}$ , $I_D = -16\text{ A}, V_{GS} = -4.5\text{ V}$		9.5	13	nC
$Q_{gs}$	Gate-Source Charge			1.3		nC
$Q_{gd}$	Gate-Drain Charge			2.2		nC

**Drain-Source Diode Characteristics and Maximum Ratings**

$I_S$	Maximum Continuous Drain-Source Diode Forward Current (Note 2)				-16	A
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current (Note 2)				-48	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -16\text{ A}$ (Note 2)			-1.2	V

**Notes:**

- $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance. For T0-263 the device is mounted on circuit board with a  $1\text{ in}^2$  pad of 2 oz. copper.
- Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

## Typical Characteristics

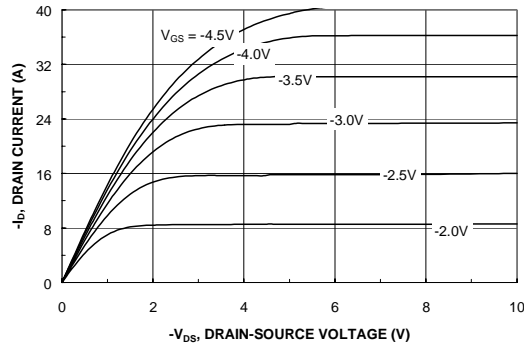


Figure 1. On-Region Characteristics.

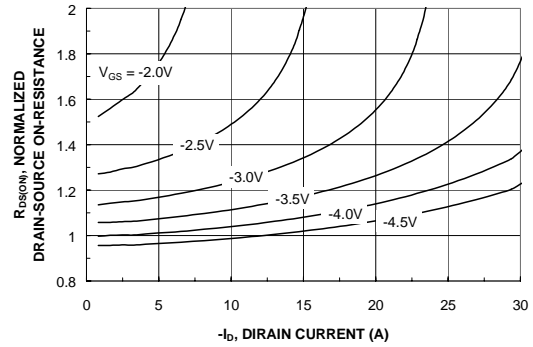


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

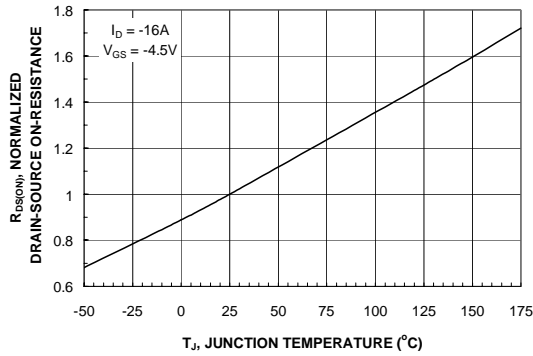


Figure 3. On-Resistance Variation with Temperature.

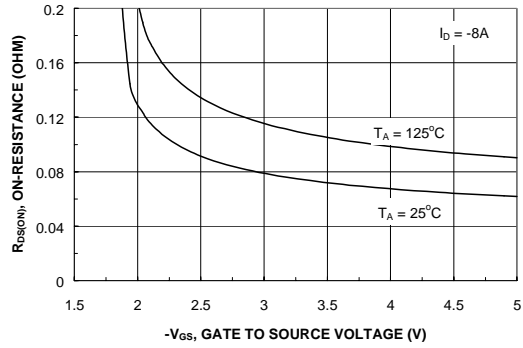


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

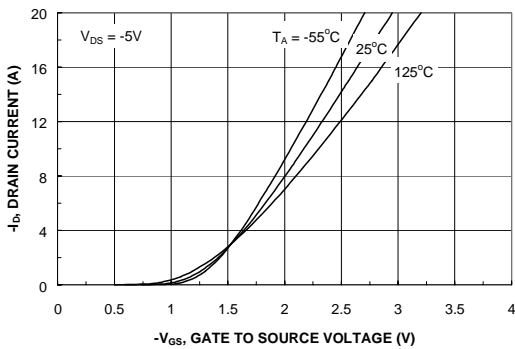


Figure 5. Transfer Characteristics.

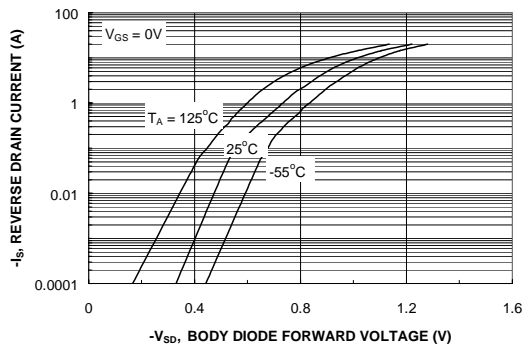


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)

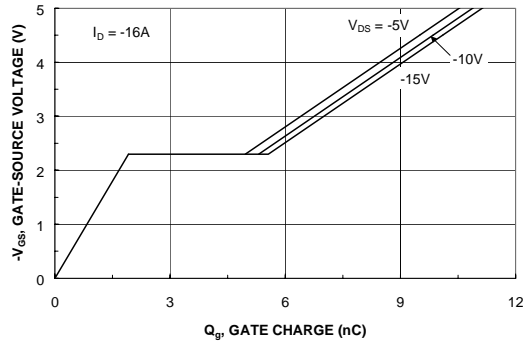


Figure 7. Gate-Charge Characteristics.

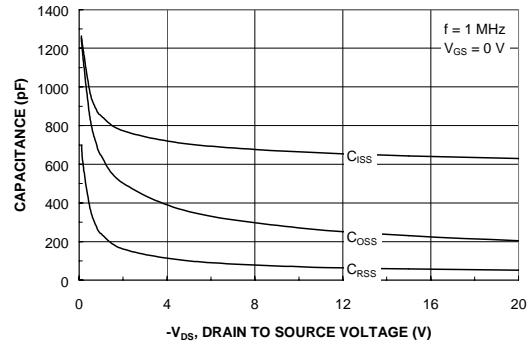


Figure 8. Capacitance Characteristics.

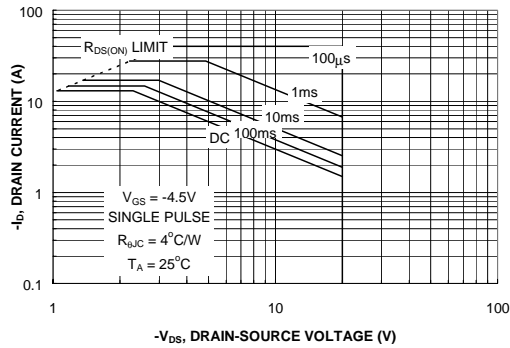


Figure 9. Maximum Safe Operating Area.

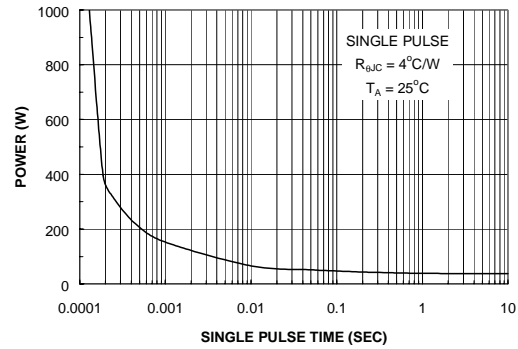


Figure 10. Single Pulse Maximum Power Dissipation.

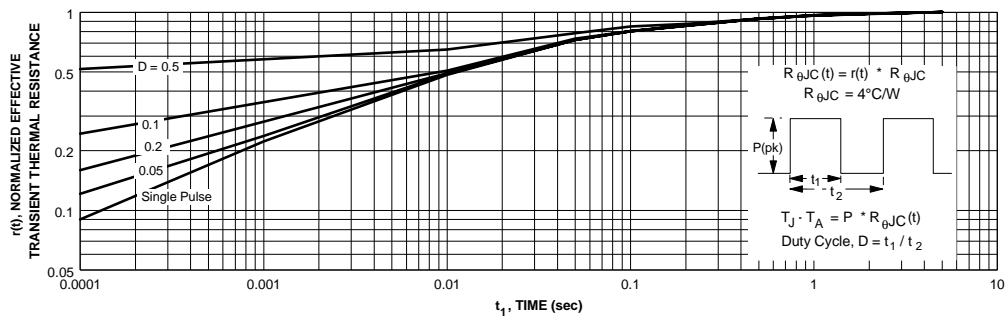


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1. Transient thermal response will change depending on the circuit board design.

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